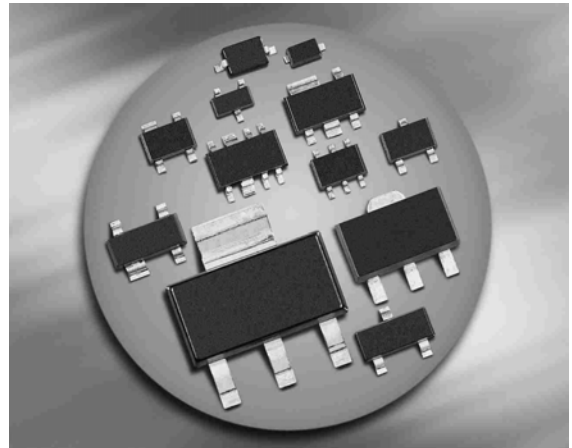
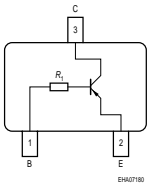


**PNP Silicon Digital Transistor**

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ( $R_1 = 47k\Omega$ )


**BCR199F/L3  
BCR199T**


Type	Marking	Pin Configuration						Package
		1=B	2=E	3=C	-	-	-	
BCR199F*	UBs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR199L3*	UB	1=B	2=E	3=C	-	-	-	TSLP-3-4
BCR199T*	UBs	1=B	2=E	3=C	-	-	-	SC75

\* Preliminary

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	50	V
Collector-base voltage	$V_{CBO}$	50	
Emitter-base voltage	$V_{EBO}$	5	
Input on voltage	$V_{i(on)}$	50	
Collector current	$I_C$	70	mA
Total power dissipation- BCR199F, $T_S \leq 128^\circ\text{C}$ BCR199L3, $T_S \leq 135^\circ\text{C}$ BCR199T, $T_S \leq 109^\circ\text{C}$	$P_{tot}$	250 250 250	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$		K/W
BCR199F		≤ 90	
BCR199L3		≤ 60	
BCR199T		≤ 165	

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**DC Characteristics**

Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	5	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
DC current gain <sup>2)</sup> $I_C = 5 \text{mA}, V_{CE} = 5 \text{V}$	$h_{FE}$	120	-	630	-
Collector-emitter saturation voltage <sup>2)</sup> $I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$	$V_{CEsat}$	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{V}$	$V_{i(off)}$	0.4	-	0.8	
Input on voltage $I_C = 2 \text{mA}, V_{CE} = 0.3 \text{V}$	$V_{i(on)}$	0.5	-	1.5	
Input resistor	$R_1$	32	47	62	k $\Omega$

**AC Characteristics**

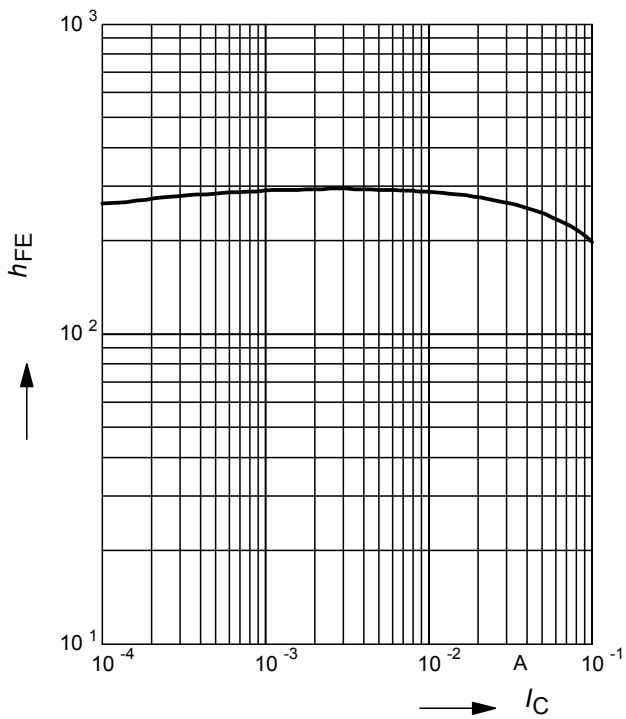
Transition frequency $I_C = 10 \text{mA}, V_{CE} = 5 \text{V}, f = 100 \text{MHz}$	$f_T$	-	200	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{V}, f = 1 \text{MHz}$	$C_{cb}$	-	3	-	-

<sup>1</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

<sup>2</sup>Pulse test:  $t < 300 \mu\text{s}; D < 2\%$

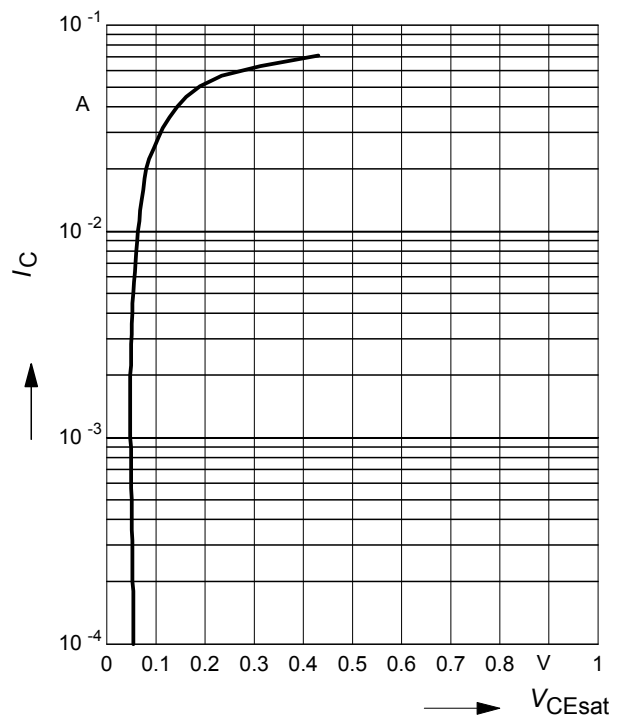
**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 5\text{ V}$  (common emitter configuration)



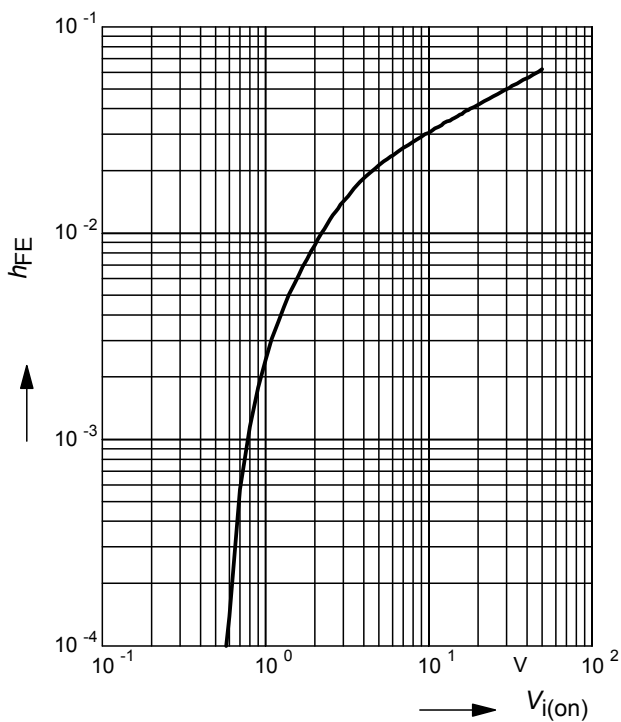
**Collector-emitter saturation voltage**

$V_{CEsat} = f(I_C), h_{FE} = 20$



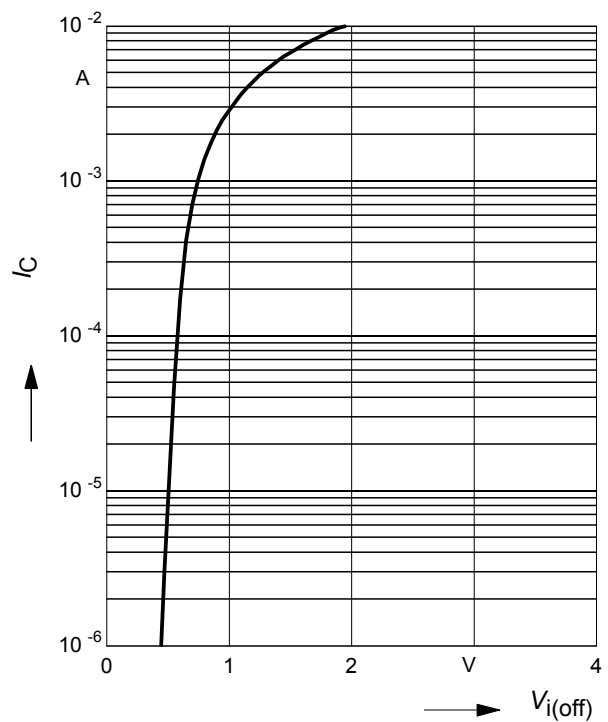
**Input on Voltage  $V_{i(on)} = f(I_C)$**

$V_{CE} = 0.3\text{ V}$  (common emitter configuration)



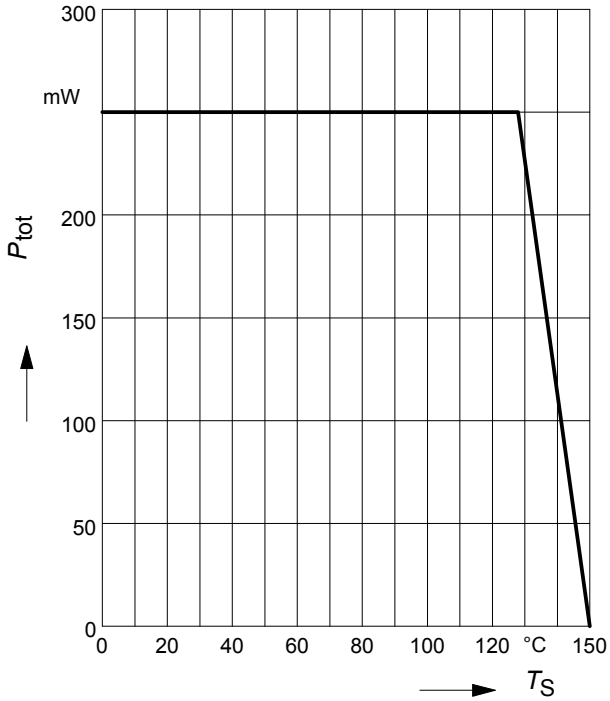
**Input off voltage  $V_{i(off)} = f(I_C)$**

$V_{CE} = 5\text{ V}$  (common emitter configuration)



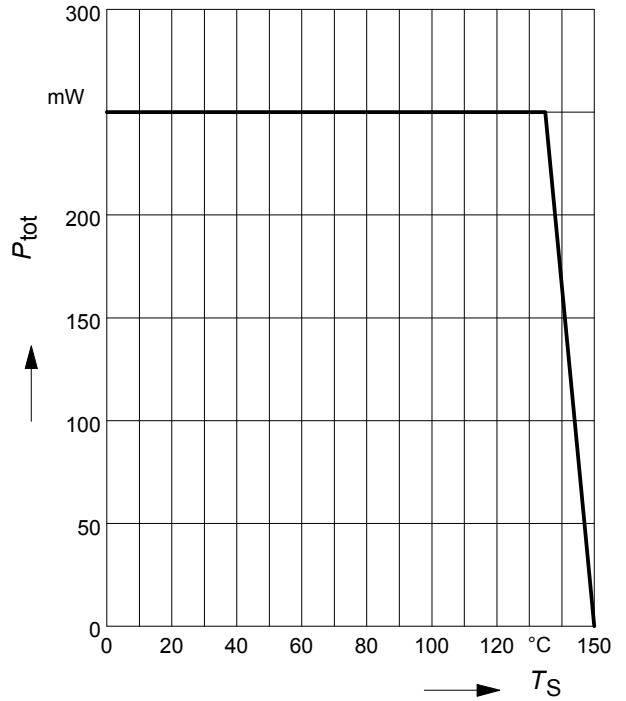
Total power dissipation  $P_{tot} = f(T_S)$

BCR199F



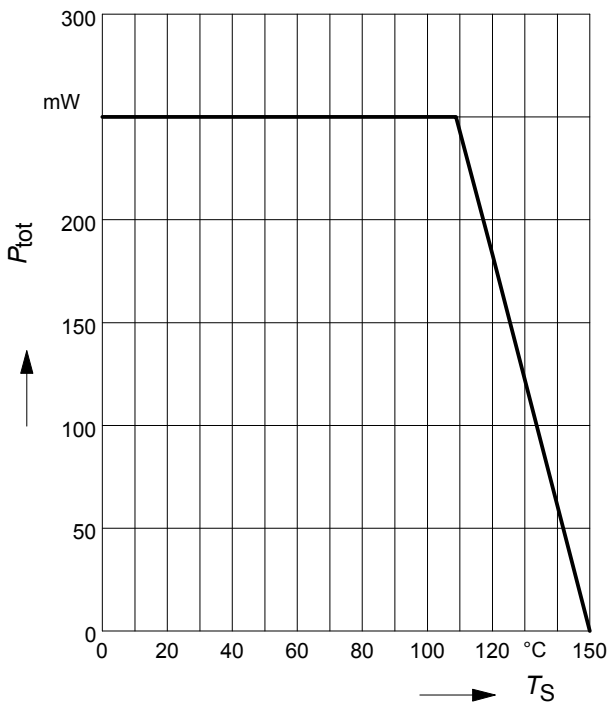
Total power dissipation  $P_{tot} = f(T_S)$

BCR199L3



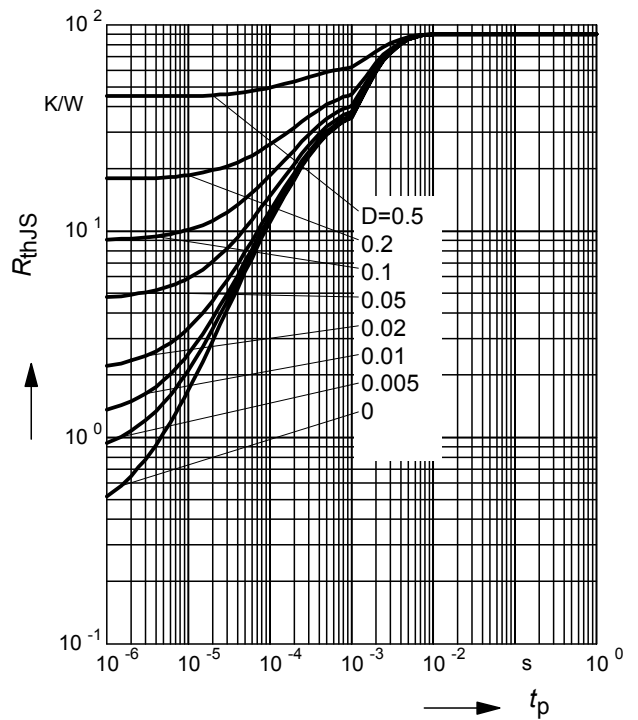
Total power dissipation  $P_{tot} = f(T_S)$

BCR199T



Permissible Puls Load  $R_{thJS} = f(t_p)$

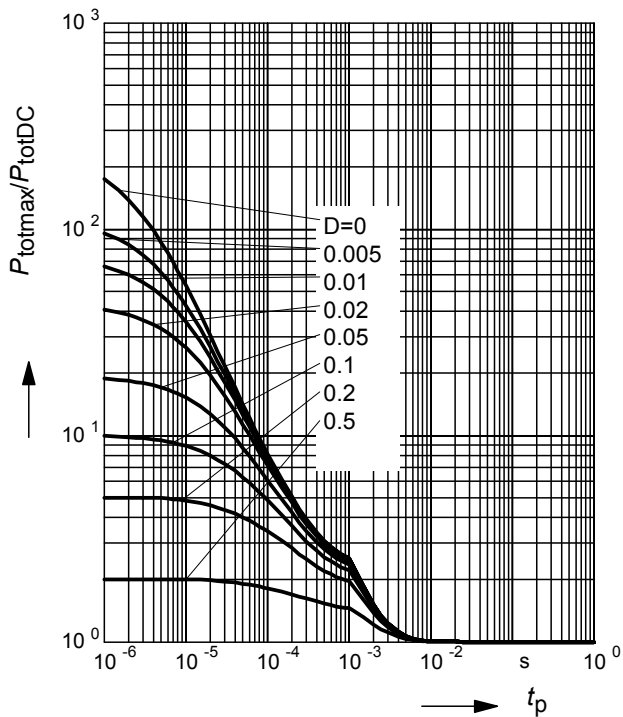
BCR199F



**Permissible Pulse Load**

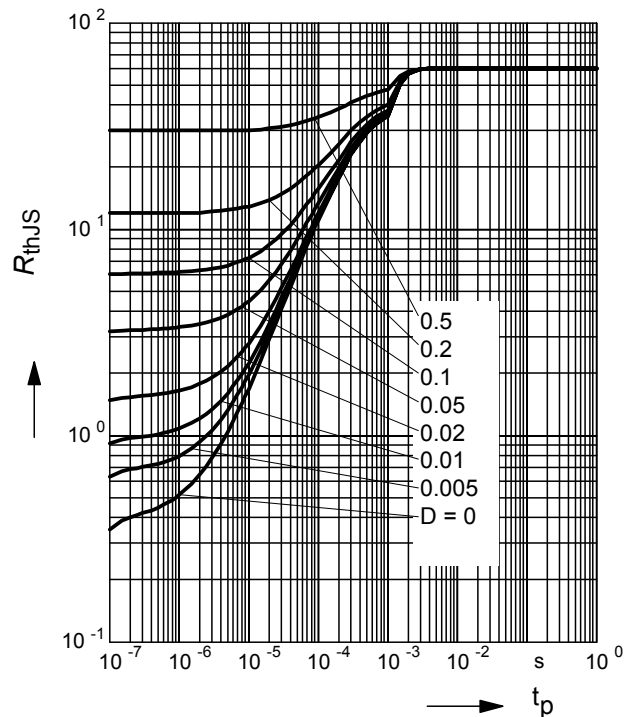
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR199F



**Permissible Puls Load  $R_{\text{thJS}} = f(t_p)$**

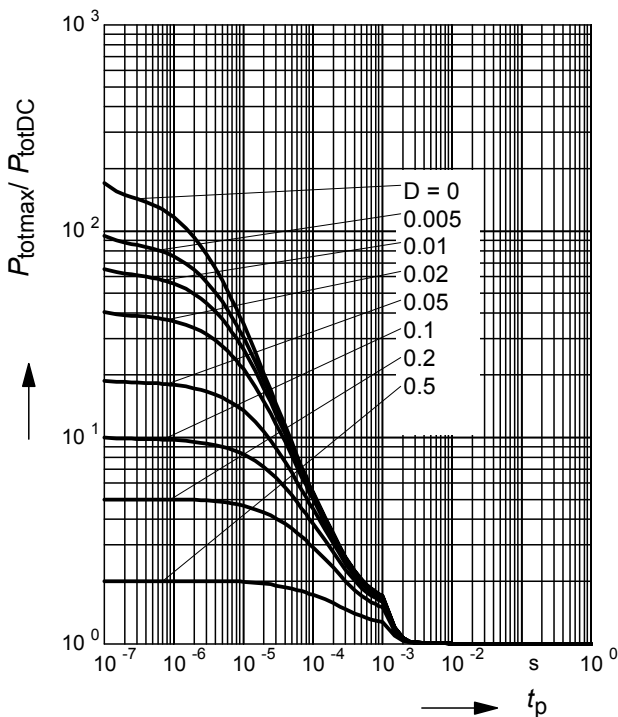
BCR199L3



**Permissible Pulse Load**

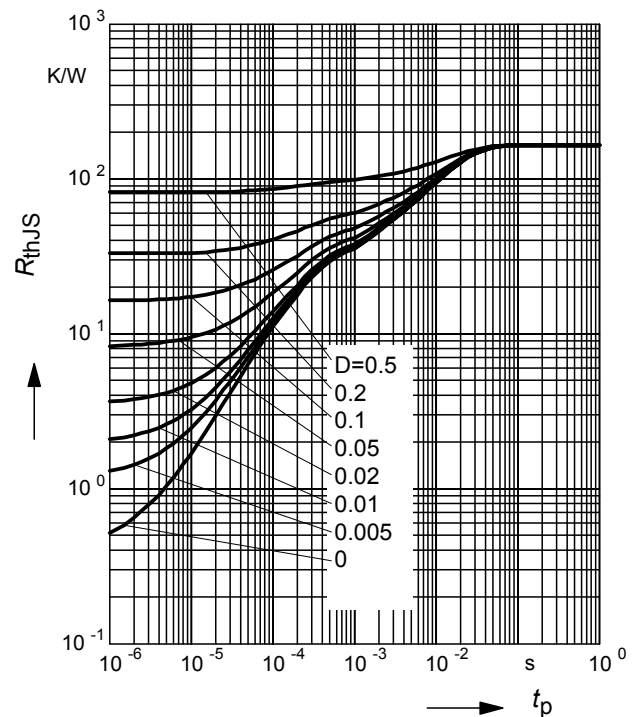
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR199L3



**Permissible Puls Load  $R_{\text{thJS}} = f(t_p)$**

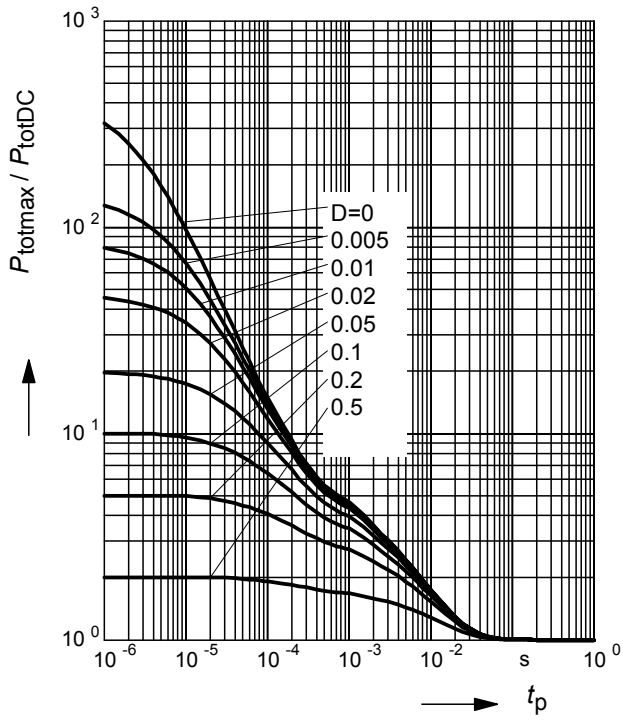
BCR199T



**Permissible Pulse Load**

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR199T



**Published by Infineon Technologies AG,  
St.-Martin-Strasse 53,  
81669 München**

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